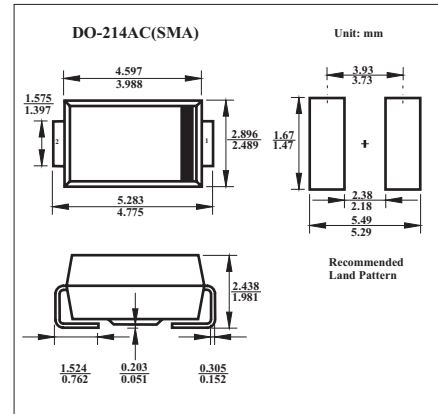


KS22 THRU KS26

■ Features

- For surface mounted applications.
- Low profile package.
- Built-in strain relief.
- Metal silicon junction, majority carrier conduction.
- Low power loss, high efficiency.
- High current capability, low forward voltage drop.
- High surge capability.



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	KS22	KS23	KS24	KS25	KS26	Unit
Maximum repetitive peak reverse voltage	V_{RRM}	20	30	40	50	60	V
Maximum RMS voltage	V_{RMS}	14	21	28	35	42	V
Maximum DC blocking voltage	V_{DC}	20	30	40	50	60	V
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	$I_{(AV)}$	2					A
Maximum average forward rectified current at TL	I_{FSM}	50					A
Maximum instantaneous forward voltage at 1.0A * 1	V_F	0.5		0.7		V	
Maximum DC reverse current * 1 $T_A=25^\circ\text{C}$ at rated DC blocking voltage $T_A=100^\circ\text{C}$	I_R	0.4					mA
		10					
Typical thermal resistance	$R_{\theta JA}$	55					$^\circ\text{C}/\text{W}$
	$R_{\theta JL}$	17					
Operating junction temperature range	T_J	-65 to +125			-65 to +150		$^\circ\text{C}$
Storage temperature range	T_{stg}	-65 to +150					$^\circ\text{C}$

* 1. Pulse test: 300ms pulse width, 1% duty cycle.

■ Marking

NO.	KS22	KS23	KS24	KS25	KS26
Marking	SS22	SS23	SS24	SS25	SS26